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# STTH2002C

## High efficiency ultrafast diode

### Features

- Suited for SMPS
- Low losses
- Low forward and reverse recovery times
- Low leakage current
- High junction temperature
- Insulated package: TO-220FPAB

### Description

Dual center tap rectifier suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in TO-220AB, D<sup>2</sup>PAK, TO-220FPAB and I<sup>2</sup>PAK, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

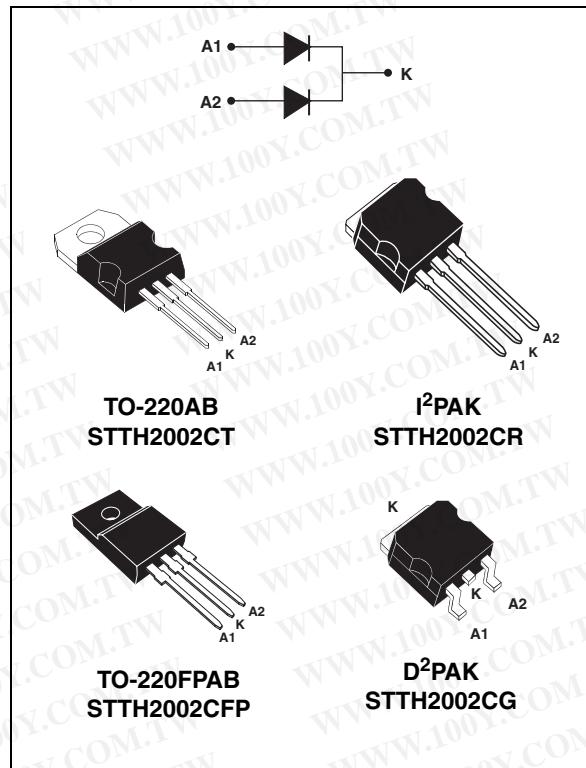


Table 1. Device summary

Symbol	Value
I <sub>F(AV)</sub>	Up to 2 x 10 A
V <sub>RRM</sub>	200 V
T <sub>j</sub> (max)	175 °C
V <sub>F</sub> (typ)	0.78 V
t <sub>rr</sub> (typ)	22 ns

# 1 Characteristics

**Table 2. Absolute ratings (limiting values, per diode)**

Symbol	Parameter			Value	Unit		
V <sub>RRM</sub>	Repetitive peak reverse voltage			200	V		
I <sub>F(RMS)</sub>	Forward rms current			30	A		
I <sub>F(peak)</sub>	Avarage forward current $\delta = 0.5$	I <sup>2</sup> PAK, D <sup>2</sup> PAK, TO-220AB	T <sub>c</sub> = 150 °C	Per diode	10	A	
			T <sub>c</sub> = 140 °C	Per device	20	A	
			T <sub>c</sub> = 130 °C	Per diode	15	A	
			T <sub>c</sub> = 115 °C	Per device	30	A	
		TO-220FPAB	T <sub>c</sub> = 120 °C	Per diode	10	A	
			T <sub>c</sub> = 85 °C	Per device	20	A	
I <sub>FSM</sub>	Surge non repetitive forward current			t <sub>p</sub> = 10 ms sinusoidal	90	A	
T <sub>stg</sub>	Storage temperature range			-65 to + 175	°C		
T <sub>j</sub>	Maximum operating junction temperature			175	°C		

**Table 3. Thermal parameters**

Symbol	Parameter			Value (max)	Unit
R <sub>th(j-c)</sub>	Junction to case	I <sup>2</sup> PAK, D <sup>2</sup> PAK, TO-220AB	Per diode	2.5	°C/W
			Per device	1.6	
			Per diode	5	
			Per device	3.8	
		TO-220FPAB	I <sup>2</sup> PAK, D <sup>2</sup> PAK, TO-220AB	0.7	
			TO-220FPAB	2.5	
R <sub>th(c)</sub>	Coupling				

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j \text{ (diode1)} = P_{\text{(diode1)}} \times R_{\text{th(j-c)}} \text{ (per diode)} + P_{\text{(diode2)}} \times R_{\text{th(c)}}$$

**Table 4. Static electrical characteristics (per diode)**

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25^\circ C$	$V_R = V_{RRM}$			10	$\mu A$
		$T_j = 125^\circ C$			6	100	
$V_F^{(2)}$	Forward voltage drop	$T_j = 25^\circ C$	$I_F = 10 A$			1.1	$V$
		$T_j = 25^\circ C$	$I_F = 20 A$			1.25	
		$T_j = 150^\circ C$	$I_F = 10 A$		0.78	0.89	
		$T_j = 150^\circ C$	$I_F = 20 A$			1.05	

1. Pulse test:  $t_p = 5 \text{ ms}$ ,  $\delta < 2\%$ 2. Pulse test:  $t_p = 380 \mu\text{s}$ ,  $\delta < 2\%$ 

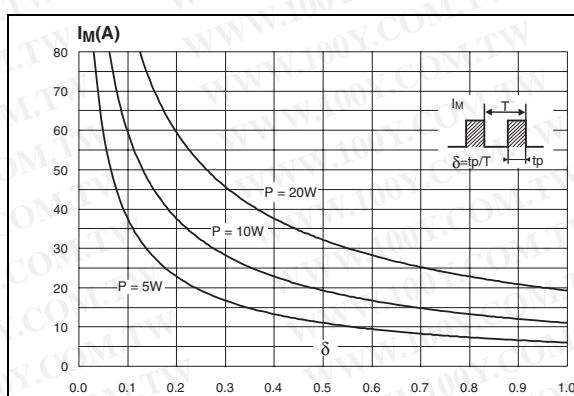
To evaluate the conduction losses use the following equation:

$$P = 0.73 \times I_{F(AV)} + 0.020 I_F^2 (\text{RMS})$$

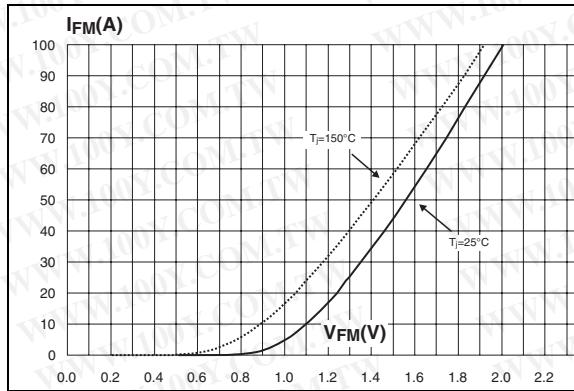
**Table 5. Dynamic electrical characteristics**

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
$t_{rr}$	Reverse recovery time	$T_j = 25^\circ C$	$I_F = 1 A$ , $V_R = 30 V$ $dI_F/dt = 100 A/\mu\text{s}$		22	27	ns
$t_{fr}$	Forward recovery time	$T_j = 25^\circ C$	$I_F = 10 A$ , $dI_F/dt = 100 A/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$			200	ns
$V_{FP}$	Forward recovery voltage	$T_j = 25^\circ C$	$I_F = 10 A$ , $dI_F/dt = 100 A/\mu\text{s}$		2.4		V
$I_{RM}$	Reverse recovery current	$T_j = 125^\circ C$	$I_F = 10 A$ , $V_R = 160 V$ $dI_F/dt = 200 A/\mu\text{s}$		7.0	9.0	A

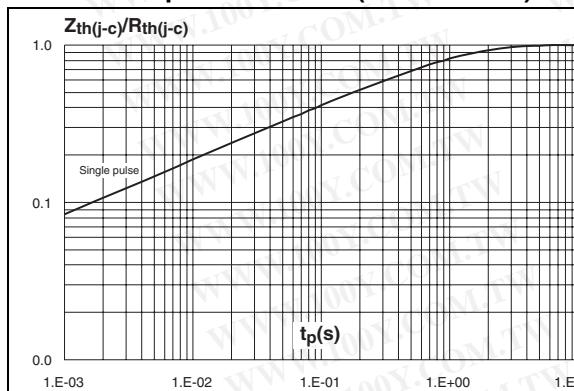
**Figure 1. Peak current versus duty cycle (per diode)**



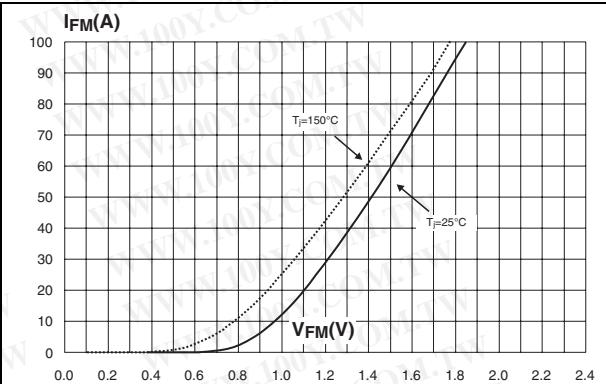
**Figure 3. Forward voltage drop versus forward current (maximum values, per diode)**



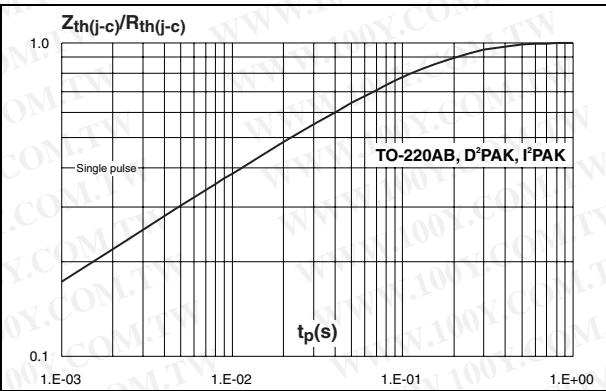
**Figure 5. Relative variation of thermal impedance junction to case versus pulse duration (TO-220FPAB)**



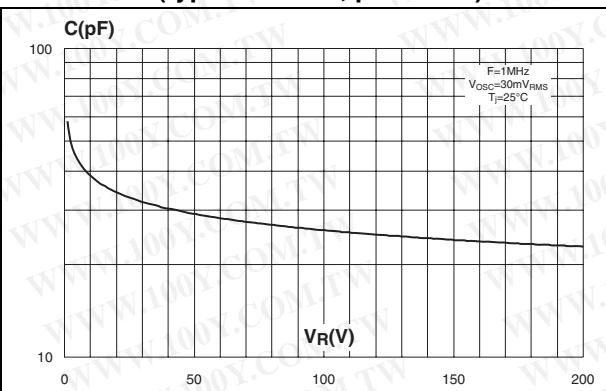
**Figure 2. Forward voltage drop versus forward current (typical values, per diode)**



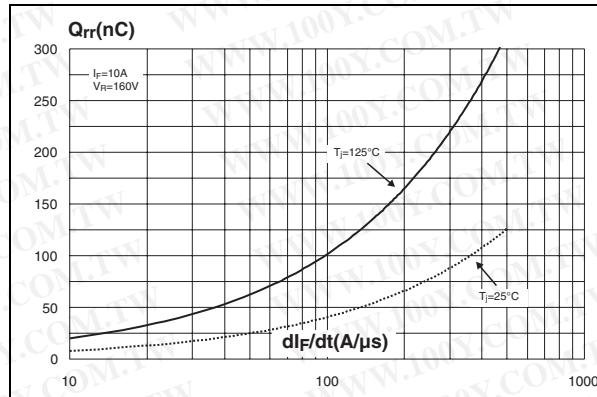
**Figure 4. Relative variation of thermal impedance junction to case versus pulse duration**



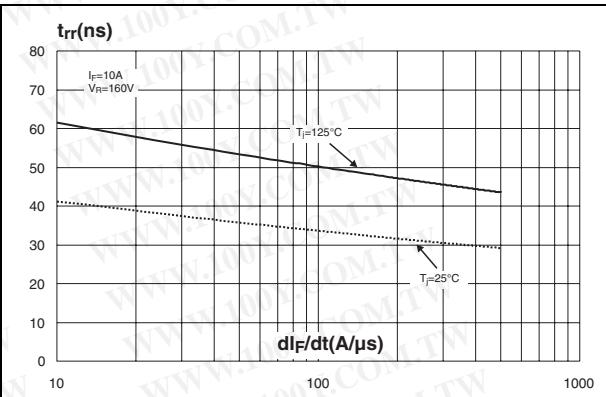
**Figure 6. Junction capacitance versus reverse voltage applied (typical values, per diode)**



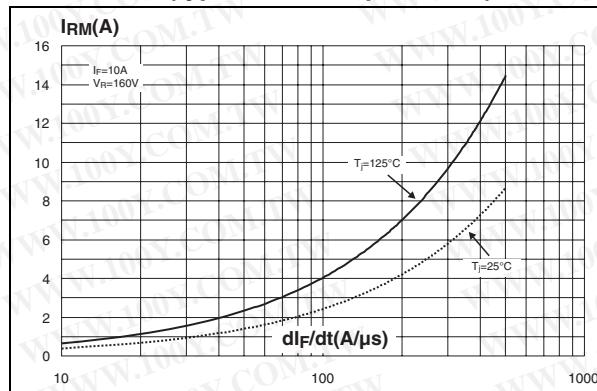
**Figure 7. Reverse recovery charges versus  $dI_F/dt$  (typical values, per diode)**



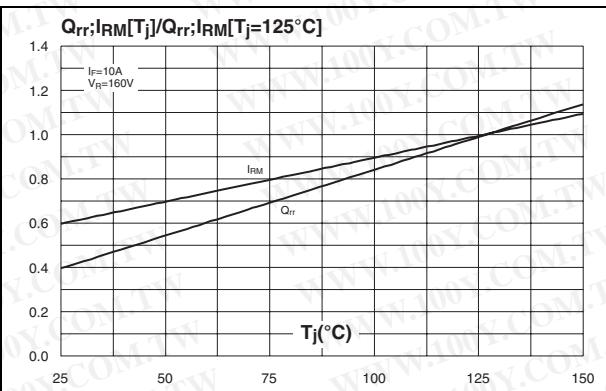
**Figure 8. Reverse recovery time versus  $dI_F/dt$  (typical values, per diode)**



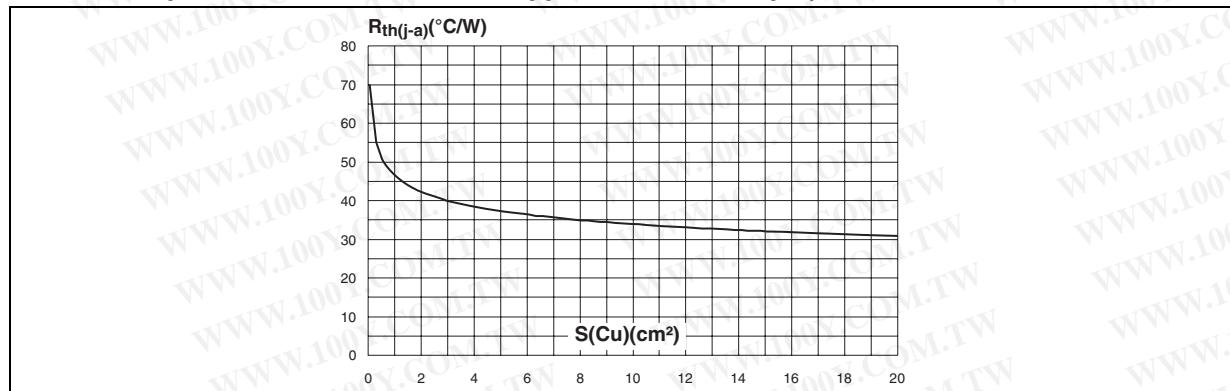
**Figure 9. Peak reverse recovery current versus  $dI_F/dt$  (typical values, per diode)**



**Figure 10. Dynamic parameters versus junction temperature**



**Figure 11. Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: 35 μm) for D<sup>2</sup>PAK**

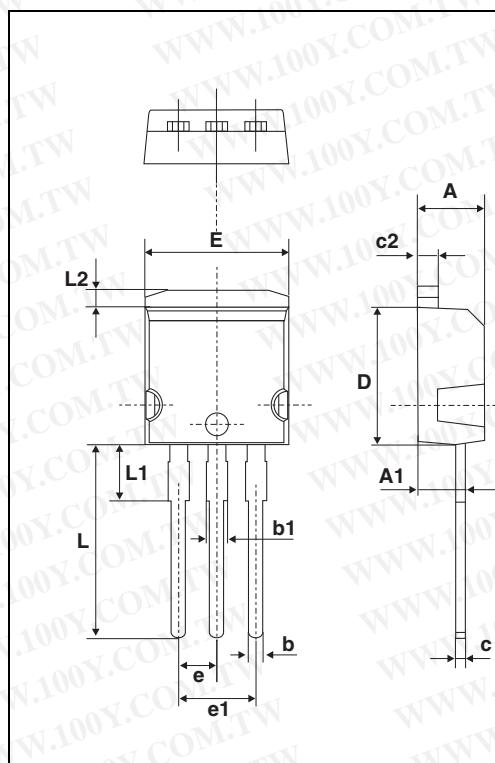


## 2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value : 0.4 to 0.6 N·n

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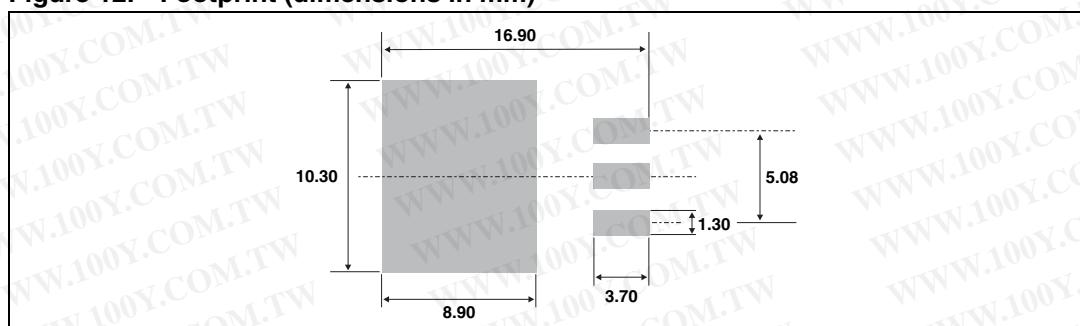
**Table 6. I<sup>2</sup>PAK dimensions**



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
A1	2.40	2.72	0.094	0.107
b	0.61	0.88	0.024	0.035
b1	1.14	1.70	0.044	0.067
c	0.49	0.70	0.019	0.028
c2	1.23	1.32	0.048	0.052
D	8.95	9.35	0.352	0.368
e	2.40	2.70	0.094	0.106
e1	4.95	5.15	0.195	0.203
E	10	10.40	0.394	0.409
L	13	14	0.512	0.551
L1	3.50	3.93	0.138	0.155
L2	1.27	1.40	0.050	0.055

**Table 7.** D<sup>2</sup>PAK dimensions

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.169		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.70		0.93	0.027		0.037
B2	1.25	1.40		0.048	0.055	
C	0.45		0.60	0.017		0.024
C2	1.21		1.36	0.047		0.054
D	8.95		9.35	0.352		0.368
E	10.00		10.28	0.393		0.405
G	4.88		5.28	0.192		0.208
L	15.00		15.85	0.590		0.624
L2	1.27		1.40	0.050		0.055
L3	1.40		1.75	0.055		0.069
R	0.40			0.016		
V2	0°		8°	0°		8°

**Figure 12.** Footprint (dimensions in mm)

**Table 8.** TO-220AB dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

**Table 9.** TO-220FPAB dimensions

Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.4	4.6	0.173	0.181
B	2.5	2.7	0.098	0.106
D	2.5	2.75	0.098	0.108
E	0.45	0.70	0.018	0.027
F	0.75	1	0.030	0.039
F1	1.15	1.5	0.045	0.059
F2	1.15	1.5	0.045	0.059
G	4.95	5.20	0.195	0.205
G1	2.4	2.7	0.094	0.106
H	10	10.4	0.393	0.409
L2	16 Typ.		0.63 Typ.	
L3	28.6	30.6	1.126	1.205
L4	9.8	10.6	0.386	0.417
L5	2.9	3.6	0.114	0.142
L6	15.9	16.4	0.626	0.646
L7	9.00	9.30	0.354	0.366
Dia.	3.00	3.20	0.118	0.126

### 3 Ordering information

**Table 10. Ordering information**

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH2002CT	STTH2002CT	TO-220AB	2.23 g	50	Tube
STTH2002CG	STTH2002CG	D <sup>2</sup> PAK	1.48 g	50	Tube
STTH2002CG-TR	STTH2002CG	D <sup>2</sup> PAK	1.48 g	1000	Tape and reel
STTH2002CR	STTH2002CR	I <sup>2</sup> PAK	1.49 g	50	Tube
STTH2002CFP	STTH2002CFP	TO-220AB	1.70 g	50	Tube

### 4 Revision history

**Table 11. Document revision history**

Date	Revision	Changes
Feb-2004	1	First issue.
23-Jun-2010	2	Updated <a href="#">Table 1</a> . Updated ECOPACK statement.

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